

ABSTRACT OF THE DISCLOSURE

A process of forming a high-definition pattern by etching is provided. A photosensitive resin layer is formed on a metal substrate material having a center line-average surface roughness Ra of up to 0.10  $\mu\text{m}$  and a maximum surface roughness Rmax of up to 1.0  $\mu\text{m}$  to form a resist pattern. Then, the photosensitive resin layer provided on the metal substrate material is exposed to light to form a resist pattern. Finally, etching is carried out to form a pattern on the metal substrate material.